

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN APM-PWR/08/3675 Notification Date 05/26/2008

SILICON LINE CHANGE FOR BIPOLAR DEVICES - BI21 PRODUCT LINE

PWR - PWR BIP/ IGBT/ RF

1/13

Table 1.	Change	Implementation	Schedule
----------	--------	----------------	----------

· · ·	
Forecasted implementation date for	23-Jul-2008
change	
Forecasted availabillity date of samples	19-May-2008
for customer	
Forecasted date for STMicroelectronics	
change Qualification Plan results availability	19-May-2008
	,
Estimated date of changed product first	25-Aug-2008
shipment	
empirient	

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	See attached list
Type of change	Waferfab process change
Reason for change	Production Optimization
Description of the change	Planar Base Island technology is ready to replace the mature Epibase technology in order to align our products to the actual Market. The line BI21 will replace the old ones B605. Feature: Improved hFE linearity and Higher fT frequency. Benefit: Better performances in switching and linear application.
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	See "N" in additional info
Manufacturing Location(s)	

Table 3. List of Attachments

Customer Part numbers list	
Qualification Plan results	

Customer Acknowledgement of Receipt	PCN APM-PWR/08/3675
Please sign and return to STMicroelectronics Sales Office	Notification Date 05/26/2008
Qualification Plan Denied	Name:
Qualification Plan Approved	Title:
	Company:
Change Denied	Date:
Change Approved	Signature:
Remark	
· ·····	

Name	Function
Di falco, Luca	Division Marketing Manager
Porto, Michele Claudio	Division Product Manager
Falcone, Giuseppe	Division Q.A. Manager

DOCUMENT APPROVAL

	APM CATANIA RELIABILITY REPORT	Date:	Feb '08
		No	07c/08

Reliability evaluation

on

BI21 for silicon line change on TIP36C

ISSUED BY	RELIABILITY DEPARTMENT	Page 1 of 8
-----------	---------------------------	-------------



Table of Contents

1.	Introduction	pg.	3
2.	Test vehicles	pg.	4
3.	Failure Criteria	pg.	5
4.	Evaluation plan and results	pg.	6
5.	Appendixes		
	- Technological Characteristics	pg.	7
	- Reliability Test Description	pg.	8



Introduction

This report is aimed to qualify the new line BI21 for line change on device TIP36C

The Qualification Reliability test trials have been performed in ST Catania Site.

The evaluation results meet ST products qualification targets, therefore the new line BI21 is qualified.

	APM CATANIA RELIABILITY REPORT	Date:	Feb '08
		No	07c/08

Test Vehicles :

Product Line	Sales Type	Package
BI21	TIP36C	TO-247



Failure Criteria :

A failed component is a device which becomes inoperative during the test or it fails on meeting the end limits foreseen in the device specification, for one or more than the parameters here below reported

Parameter Power BIPOLAR Main Parameter

Collector Leakage Current (Icbo or Iceo or Ices, etc...) Emitter Leakage (Iebo) HFE, Vcesat, Vbesat, Vf Breakdown Voltage (BVcbo, BVceo,Vbces, Bvebo)

ISSUED BY	RELIABILITY DEPARTMENT	Page 5 of 8
-----------	---------------------------	-------------



Reliability Evaluation Plan and results

D.U.T.: TIP36C LINE: BI21 PACKAGE: TO-247

Test	Conditions	S.S.	Requirement	Results
H.T.S.	TA=150℃	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
T.H.B.	TA=85℃ - RH=85% Vbias= 50V	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
H.T.R.B.	T.A.=150℃ Vdd=-80V	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
PRESSURE POT	TA=121℃ - PA=2Atm	77 x 1 Lot	Parameter deviation within spec. limits at 96 hours.	No parameter deviation out of spec. limits at 96 hours.
THERMAL CYCLES AIR TO AIR	TA=-65℃ TO 150℃ 1 HOUR / CYCLE	77 x 1 Lot	Parameter deviation within spec. limits at 500 cycles.	No parameter deviation out of spec. limits at 500 cy
THERMAL FATIGUE	∆TC=70℃ - Pd=24W	77 x 1 Lot	Parameter deviation within spec. limits at 10k cycles.	No parameter deviation out of spec. limits at 10Kcy.

ISSUED BY	RELIABILITY DEPARTMENT	Page 6 of 8
-----------	---------------------------	-------------



Technological Characteristics

D.U.T.: TIP36C LINE: BI21 PACKAGE: TO-247

	Technology:	PLANAR PNP		
DIE	Material:	Silicon	Passivation :	P-Vapox
	Metallization – Front : - Back :	Al/Si Au/Cr/Ni/Au	Dimensions :	4030 x 3680 um ²
			Frame and lead material:	Raw Copper
DIE ATTACH	Soft Solder	FRAME	Frame coating :	Full Ni/NiP except Die Pad Area
			Lead coating :	Sn 100%
WIRE			Material :	Al/Mg Base Al Emitter
BOND	Ultrasonic	WIRE	Diameter :	7 mils Base 15 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

PRODUCTION PLACES: WAFER PROCESSING: ASSEMBLY LOCATION: QA LOCATION: Ang Mokio (Singapore) AIN SEBAA. (Morocco) AIN SEBAA. (Morocco)

ISSUED BY DEPARTMENT Page 7 of 8	ISSUED BY	RELIABILITY DEPARTMENT	Page 7 of 8
----------------------------------	-----------	---------------------------	-------------



Reliability Test Description

High Temperature Reverse Bias (HTRB)

This test is performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and simultaneously reverse biased. The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, etc...

High Temperature Storage (HTS)

This stress test is performed to check the device life in a high temperature ambient. Specimens are put for a period of time inside a stove in free air. Detectable failure mechanisms are presence of contaminants and metal corrosion.

Temperature Humidity Bias (THB)

This test is performed to check the device life in a high humidity ambient. Specimens are subjected to a permanent bias in a climatic chamber in the presence of steam. Detectable failure mechanisms are metal corrosion and molding defects.

Pressure Pot

This test is performed in order to check device life in a high humidity ambient in an accelerated way. Specimens are subjected for a period of time inside an autoclave in the presence of steam and pressure. Detectable failure mechanism is metal corrosion.

Thermal Fatigue

This test is performed to demonstrate the quality and reliability of devices exposed to cyclic variation in electrical stress between "on" and "off" conditions and resultant cyclic variation in device and case temperatures (thermo-mechanical stress). The purpose of this test is to detect assembly defects: improper die-attach, bonding weakness and thermal mismatch among various components of the package.

	RELIABILITY	
ISSUED BY	DEPARTMENT	Page 8 of 8

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2008 STMicroelectronics - All rights reserved.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morroco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com